DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN APPLICATION DATA SHEET (37 CFR 1.76)

Electronic Version v11
Stylesheet Version v10

Title	of
Invent	ion

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE HAVING DIVIDED BIT LINES

As the below named inventors, we declare that:

This declaration is directed to the invention titled: "NONVOLATILE SEMICONDUCTOR MEMORY DEVICE HAVING DIVIDED BIT LINES"

We believe that we are the original and first inventors of the subject matter which is claimed and for which a patent is sought;

We have reviewed and understand the contents of the above-identified application, including the claims, as amended by any amendment specifically referred to above;

We acknowledge the duty to disclose to the United States Patent and Trademark Office all information known to us to be material to patentability as defined in 37 CFR 1.56, including for continuation-in-part applications, material information which became available between the filing date of the prior application and the national or PCT International filing date of the continuation-in-part application.

All statements made herein of own knowledge are true, all statements made herein on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like are punishable by fine or imprisonment, or both, under 18 U.S.C. 1001, and may jeopardize the validity of the application or any patent issuing thereon.

FULL NAME OF INVENTORS:

Inventor 1: Ching-Hsiang Hsu	Inventor
Signature :	Citizen of : TW
Inventor 2: Ching-Sung Yang	Inventor
Signature :	Citizen of : TW

COMBINED DECLARATION AND POWER OF ATTORNEY

as the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name and that I believe I am an original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE HAVING DIVIDED BIT LINES

the	specification of which	1				
X	is attached hereto.					
	was filed on					
	as Application Seria	al No	and was amended on		•	
app	ecification, including the I acknowledge the olication in accordance I hereby claim foreitication(s) for patent of incation for patent or in	ne claims, as amended duty to disclose info with Title 37, Code of gn priority benefits un or inventor's certificate	and understand the content of by any amendment referred rmation which is material to of Federal Regulations, § 1.5 der Title 35, Untied States Content of the listed below and have also it aving a filing date before that	d to above. the paten 66(a). code, § 119 dentified be	tability of this of any foreign low any foreign	
-	ority is claimed:	/- \-				
Pri	or Foreign Application	(s):				
	Number	Country	Date Filed(yyyy/mm/dd)	Yes	No	
	90107844	Taiwan, R.O.C.	2001/4/2	-	X	
traı		ne Patent and Tradem (Reg. No. 43,33	6) Chanette Armstrong	rith: (Reg. No (Reg. No	olication and to o. 39,081) o. 44,011) o. 38,962)	
_	SEND CORRESPONDENCE TO:		_ ,, , , , _ , _	DIRECT TELEPHONE CALLS TO: (Name and telephone number)		
J.C. Patents, Inc. 4 Venture, Suite 250 Irvine, CA 92618 (949) 660-0761			Jiawei Huang (949) 660-0762			

COMBINED DECLARATION AND POWER OF ATTORNEY CONTINUED

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patents issued thereon.

Signature:	Date: _	Aug. 27,	200/
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Sole or First Joint Inventor: Chirig-Hsiang Hsu

Citizenship: Taiwan, R.O.C. Residence and Post Office Address: No. 100-28, Chien Chung Rd., Hsinchu, Taiwan, R.O.C.

Citizenship:

Residence and Post Office Address: No. 61, Lane 425, Ta-Hsi Rd., Sec. II, Hsi-Hu Chen, Chang-Hua Hsien, Taiwan, R.O.C.